



安徽富信半导体科技有限公司

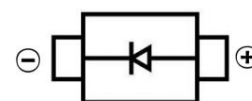
ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

S3ABF-S3MBF

SMBF General Purpose Rectifier Diode 通用整流二极管

■Features 特点

- Glass passivated junction 玻璃钝化结
- Low reverse leakage current 低反向漏电流
- Low forward voltage drop 低正向压降
- High current capability 高电流能力
- Surface mount device 表面贴装器件
- Case 封装:SMBF



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	S3A BF	S3B BF	S3D BF	S3G BF	S3J BF	S3K BF	S3M BF	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V_R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I_F	3							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	100							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	13							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	150 $^{\circ}\text{C}$, -55to+150 $^{\circ}\text{C}$							

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Condition 条件
Forward Voltage 正向电压	V_F			1.1	V	$I_F=3\text{A}$
Reverse Current 反向电流	I_R			5 250	μA	$V_R=V_{RRM}$ $T_a=25^{\circ}\text{C}$ $T_a=125^{\circ}\text{C}$
Diode Capacitance 二极管电容	C_D		60		pF	$V_R=4\text{V}, f=1\text{MHz}$



■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

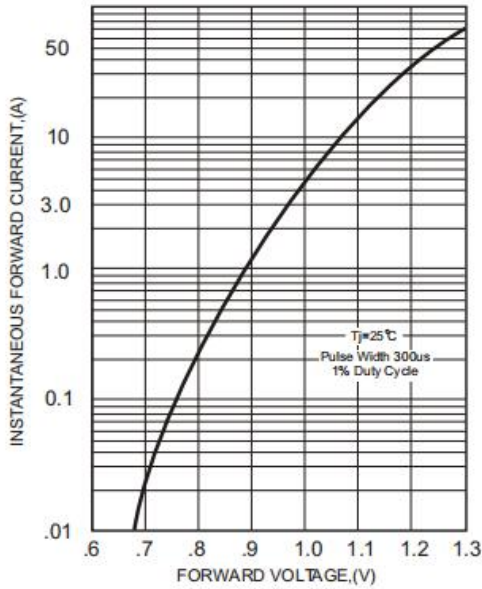


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

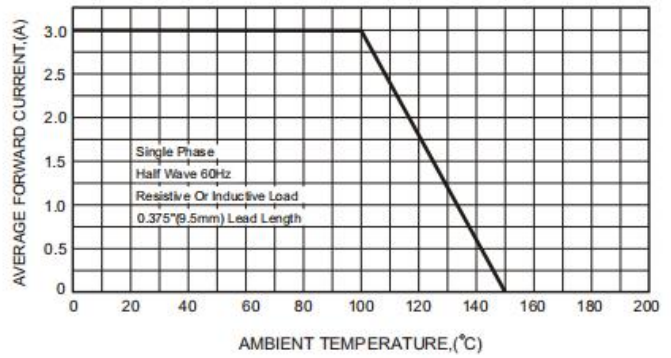


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

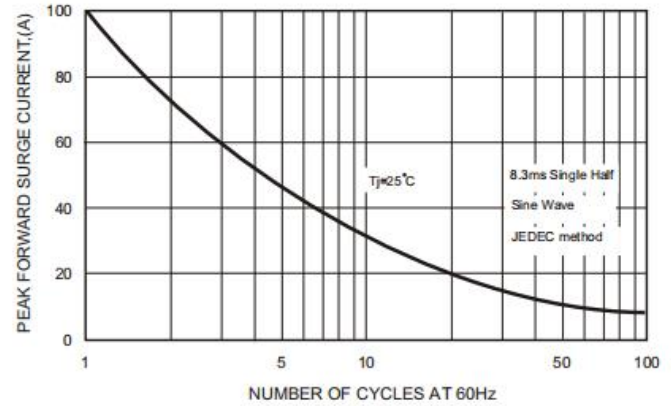


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

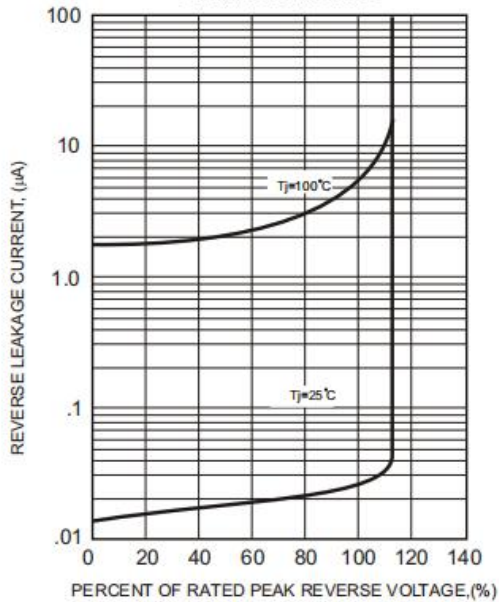
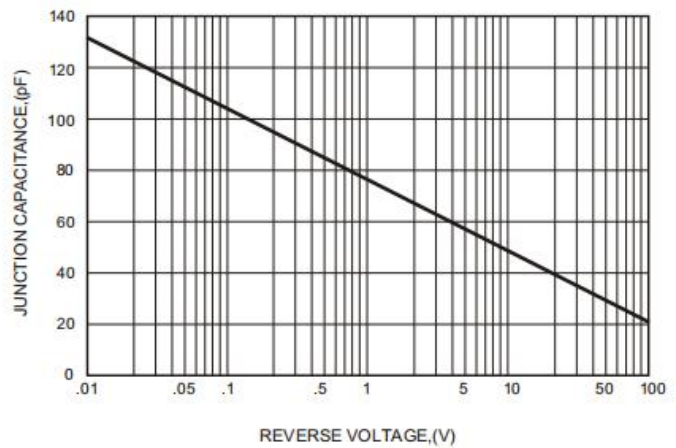
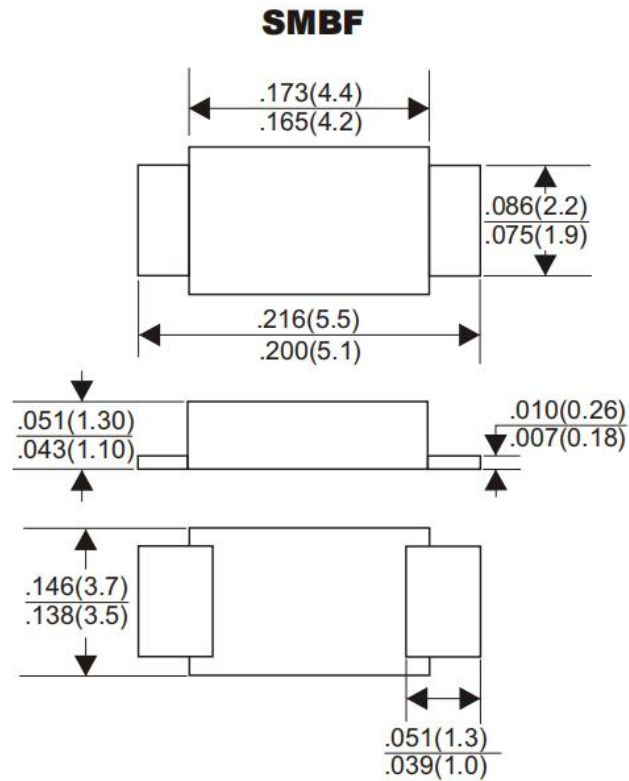


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)